

Silicon PNP transistor epitaxial type 6A885

[Applications]

High side switches
Compact relay, Motor drivers

[Feature]

Shrunked die size for small package assembly
High collector current $I_C = -650\text{mA}$
Small saturation voltage at high current $V_{CE(sat)} = -0.65\text{V}$ at $I_C = -500\text{mA}$
Excellent hFE linearity

[Absolute maximum ratings (Ta=25°C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-Base Voltage	VCBO	-25	V
Collector-Emitter Voltage	VCEO	-20	V
Emitter-Base Voltage	VEBO	-4	V
Peak Collector Current	ICM	-1000	mA
Collector Current	IC	-650	mA
Junction Temperature	Tj	150	C
Storage Temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25°C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base Breakdown Voltage	BVCBO	-25	-	-	V	$I_C = -10\mu\text{A}$, $I_E = 0\text{A}$
Collector-Emitter Breakdown Voltage	BVCEO	-20	-	-	V	$I_C = -100\mu\text{A}$, $I_B = 0\text{A}$
Emitter-Base Breakdown Voltage	BVEBO	-4	-	-	V	$I_E = -10\mu\text{A}$, $I_C = 0\text{A}$
Collector Cut-off Current	ICBO	-	-	-1	μA	$V_{CB} = -25\text{V}$, $I_E = 0\text{A}$
Emitter Cut-off Current	IEBO	-	-	-1	μA	$V_{EB} = -2\text{V}$, $I_E = 0\text{A}$
DC Current Gain	hFE	150	-	800	-	$V_{CE} = -4\text{V}$, $I_C = -100\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-0.35	-0.65	V	$I_C = -500\text{mA}$, $I_B = -25\text{mA}$
Transition Frequency	fT	-	180	-	MHz	$V_{CE} = -6\text{V}$, $I_E = 10\text{mA}$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

